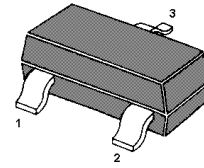


MMBTSC945

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into five groups R, O, Y, P and L, according to its DC current gain. As complementary type the PNP transistor MMBTSA733 is recommended.



1.BASE 2.EMITTER 3.COLLECTOR

SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group R O Y P L	h_{FE}	40	-	80	-
	h_{FE}	70	-	140	-
	h_{FE}	120	-	240	-
	h_{FE}	200	-	400	-
	h_{FE}	350	-	700	-
Collector Base Cutoff Current at $V_{CB} = 40\text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 10\text{ mA}$	f_T	-	300	-	MHz
Output Capacitance at $V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{OB}	-	2.5	-	pF

TOP DYNAMIC

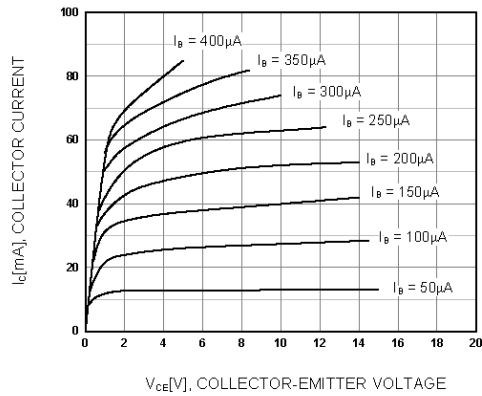


Figure 1. Static Characteristic

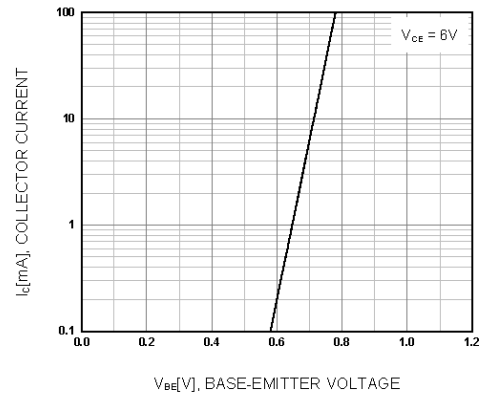


Figure 2. Transfer Characteristic

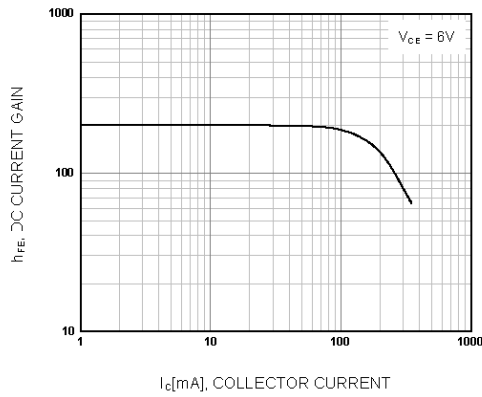


Figure 3. DC current Gain

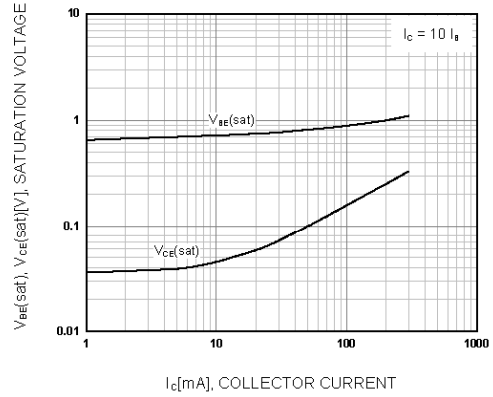


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

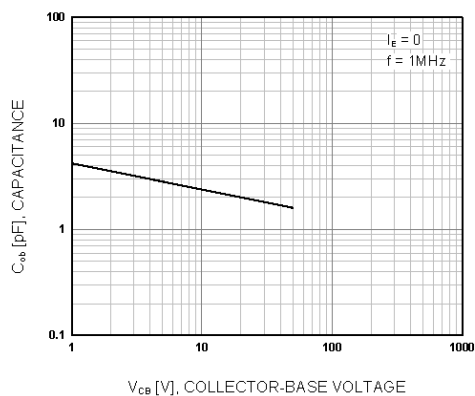


Figure 5. Output Capacitance

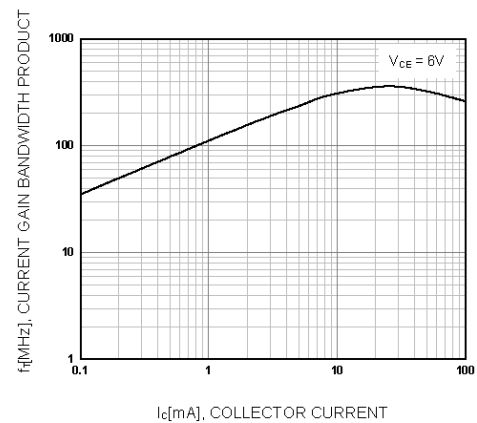


Figure 6. Current Gain Bandwidth Product